



Detectors for Single-Photon counting applications at visible and near-infrared wavelengths

Raphael Jöhren¹, Wladimir Buglak¹, Volker Hannen¹, Jonas Mader¹, Wilfried Nörtershäuser^{2,3}, Rodolfo Sánchez³ and Christian Weinheimer¹

¹ Institut für Kernphysik, Universität Münster
² Institut für Kernchemie, Universität Mainz
³ GSI Helmholtzzentrum für Schwerionenforschung, Darmstadt

June 29th, 2010

Eisenach, June 29th, 2010

Raphael Jöhren





Outline:

- Application: The SPECTRAP experiment
- Detector test setup in Münster
- Characterization of APDs (1100 nm detection) \rightarrow Results for RMD S0223 APD
- Test setup calibration for Single-Photon measurements
- Detectors for NIR (1500 nm) Single Photon detection





Laserspectroscopy experiments at GSI:

- Probing QED in extreme electromagnetic fields (up to 10¹⁶ V/cm and 10⁵ T) of Highly Charged lons, where QED cannot be described by perturbation theory
 - \rightarrow Precise measurements of Hyperfine-transitions in HCI (H-like, Li-like ions)
- HCI to observe: H-like ²⁰⁷Pb⁸¹⁺

WESTFÄLISCHE WILHELMS-UNIVERSITÄT

MÜNSTER

H-like ²⁰⁹Bi⁸²⁺ Li-like ²⁰⁹Bi⁸⁰⁺

Measurements of HFS transitions in two bismuth charge states allows to disentangle nuclear structure effects and QED effects





<u>+</u>

Westfälische Wilhelms-Universität Münster

Laserspectroscopy with SPECTRAP







Why Single-Photon Counting?



 Count rates depend on the lifetimes of the observed hyperfine states

es liquid nitrogen vessel superconductoing magnet Penning trap liquid helium vessel

Thesis D. Hampf, WWU Münster, 2008

- Due to small solid angle and light losses count rates of O(kHz) and lower are expected
- The wavelength region from 300 nm 1100 nm could be covered by Avalanche Photodiodes (APDs) → higher QE compared to PMTs

Count rate estimates:

isotope	wavelength	photon rate	detector	expected count rate
$^{209}{\rm Bi}^{82+}$	244 nm	$(625\pm225)\rm kHz$	CPMs	$(125 \pm 45) \mathrm{kHz}$
$^{207} Pb^{81+}$	1020 nm	$(6, 5 \pm 2, 1) \mathrm{kHz}$	APDs	$(1, 3 \pm 0, 4) \mathrm{kHz}$
$^{209}\text{Bi}^{80+}$	1555 nm	$(3,4\pm1,0)\mathrm{kHz}$	Hybrid PMTs	$(440 \pm 130)\mathrm{Hz}$

\rightarrow Single photon counting capability required

<u>+</u>



SPECTRAP: Setup





Eisenach, June 29th, 2010

6/18

Characterizing APDs: Test Setup



10⁻⁷ mbar vacuum chamber

WESTFÄLISCHE WILHELMS-UNIVERSITÄT

MÜNSTER

- Cryogenic cooling to near LN₂ temperature (-178°C @ detector)
- HV supply up to 4 kV, adjustable on 0.1 V scale
- LabVIEW based temperature control
- Single photons produced by applying 20 ns wide pulses (800 mV amplitude) to a LED
- Grating spectrograph for determination of spectral response using a continuous light source
- Specially designed preamp layout:
- → Preamp equivalent noise level below 1 keV FWHM (without detector)



<u>-</u>

Westfälische Wilhelms-Universität Münster

Characterizing APDs: Test Setup







Westfälische Wilhelms-Universität Münster

Investigated APD Types



Avalanche Photo Diodes are a special type of PIN diodes, operated at high bias voltages. Primary charge carriers are amplified by an internal avalanche process

Suitable for 300 – 1100 nm

 \rightarrow H-like ²⁰⁷Pb⁸¹⁺ transition at SPECTRAP (1020 nm)

Investigated APD types:

1) RMD S1315 (13 x 13 mm², without substrate):

- Have been investigated for ESR measurements due to their large area
- Problems: No stable operation achieved
- 2) Hamamatsu S8664-20K (2 mm diameter)
 - Problems: Gain at best SNR not sufficient
- 3) RMD S0223 (2 x 2 mm², Al₂O₃ backing,)
 - High gain at optimum Noise to Gain Ratio
 - Stable operation

S0223





WESTFÄLISCHE WILHELMS-UNIVERSITÄT Characterizing APDs: Measurements



- Photon Gain measured with short LED pulses which are coupled to the APD via light guide
- Gain determination by comparing amplitudes of LED pulses at different bias volages
- Mean amplitude of LED pulse at low bias voltage is defined as gain = 1
- Electronic test pulse simulates 100 keV (1 MeV) signal



Westfälische Wilhelms-Universität Münster



- Noise value is given by FWHM of the LED pulse
- Best Noise to Gain Ratio of S0223 APD at temperatures around -178°C and at 1480V bias
- Gain of about 7500 at best SNR achieved with S0223 APD
- S8664-20k and S1315 APDs exhibit large fluctuations in measured noise characteristics
- Stable operation with S0223 APD

Gain of Hamamatsu S8664-20k type APD and RMD APD types S1315 and S0223





 Noise value is given by FWHM of the LED pulse

WILHELMS-UNIVERSITÄT

- Best Noise to Gain Ratio of S0223 APD at temperatures around -178°C and at 1480V bias
- Gain of about 7500 at best SNR achieved with S0223 APD
- S8664-20k and S1315 APDs exhibit large fluctuations in measured noise characteristics
- Stable operation with S0223 APD

Noise to Gain Ratio of Hamamatsu S8664-20k type APD and RMD APD types S1315 and S0223







- Channel Photomultiplier as reference detector for Single-Photon sensitivity tests (well known single photon response and QE)
- PerkinElmer CPM 1993 with 2 mm aperture at the same position as S0223 APD
- Determine dark count rate and signal rate for different settings of pulsed LED
 → extract photon rates incident on APD





Extracted photon rates



 Assuming a QE = (4±0.5)% for the CPM at 635 nm, we can calculate incident photon rates for the given 2 mm aperture

Westfälische Wilhelms-Universität

- APD dark count rate < 10 Hz at 60 mV threshold
- Mean value for Photo Detection Efficiency of S0223 APD at 635 nm: 62% - 79%
- Consistent with QE = 68% from RMD datasheet



<u>+</u>

Westfälische Wilhelms-Universität Münster

Detectors for 1500 nm Transitions



Intevac Intensified Photodiodes (IPD)



- Active diameter: Ø 1 mm
- Dark counts: ~2 MHz @ -40°C
- QE @ 1500 nm: ~20%
- Measuring time per wavelength:

$$t = \frac{n_{\sigma} \cdot (dark \ counts)}{S^2 \cdot \epsilon^2} = 92s$$

with S = 3.4 kHz, n_{σ} = 3 and ε = QE • CE (65%) = 0.13

→ Status: 2 devices ordered

Hamamatsu NIR PMT Module



- Active diameter: Ø 18 mm detection diameter for collimated light, Ø 1.6 mm effective PMT diameter
- Dark counts: ~200 kHz @ -60°C
- QE @ 1500 nm: ~2%
- Measuring time per wavelength:

$$t = \frac{3 \cdot 2 \cdot 10^5 \, 1/s}{3400^2 \, 1/s^2 \cdot 0.017^2} = 538s$$

→ Status: Device obtained on a loan basis from Hamamatsu and tested



Intevac IPD



Operating principle:

- Primary electron from InGaAs Cathode (930 nm – 1650 nm)
- Electrostatic acceleration of primary electron onto an APD
- Up to 1000 charge carriers per incident electron
- Another amplification by factor ~10 due to the APD's avalanche process



Road map:

- Build custom housing for operation and cooling
- Investigate dark count rate as shown for InGaAsP type IPD (up to 1300 nm):



HPMT SN 201, 1064 nm Wavelength

Eisenach, June 29th, 2010

Raphael Jöhren

Test: Hamamatsu NIR PMT Module



Test results:

- Dark count rate of 300 kHz observed at 25°C ambient temperature
- At 9°C ambient temperature: 160 kHz dark counts, but signal rate decreased by factor 2









- The SPECTRAP experiment will perform precision measurements of hyperfine transitions in selected H-like and Li-like HCI to test QED
- Due to long lifetimes of these states and limited solid angle we expect fluorescence photon rates in the kHz region
 → Single-Photon detection capabilities required
- APDs provide high QE and moderate gain at visible and NIR wavelengths up to 1100 nm (SPECTRAP: H-like ²⁰⁷Pb⁸¹⁺ transition at 1020 nm)
- Current tests at 635 nm have shown a Photo Detection Efficiency (PDE) in the 62% - 79% range at dark count rates < 10 Hz
- Determination of PDE at 1020 nm requires a calibrated Single-Photon source at that wavelength
 → Possibility of using correlated photons
- Detectors for 1555 nm Li-like ²⁰⁹Bi⁸⁰⁺ transition under investigation